

Page i

INTEGRATED CIRCUITS, SILICON MONOLITHIC,

BIPOLAR 9-BIT ODD/EVEN PARITY

GENERATOR/CHECKER,

BASED ON TYPE 54LS280

ESCC Detail Specification No. 9208/001

ISSUE 1 October 2002



Document Custodian: European Space Agency - see https://escies.org



LEGAL DISCLAIMER AND COPYRIGHT

European Space Agency, Copyright © 2002. All rights reserved.

The European Space Agency disclaims any liability or responsibility, to any person or entity, with respect to any loss or damage caused, or alleged to be caused, directly or indirectly by the use and application of this ESCC publication.

This publication, without the prior permission of the European Space Ageny and provided that it is not used for a commercial purpose, may be:

- copied in whole in any medium without alteration or modification.
- copied in part, in any medium, provided that the ESCC document identification, comprising the ESCC symbol, document number and document issue, is removed.



european space agency agence spatiale européenne

Pages 1 to 27

INTEGRATED CIRCUITS, SILICON MONOLITHIC,

BIPOLAR 9-BIT ODD/EVEN PARITY

GENERATOR/CHECKER,

BASED ON TYPE 54LS280

ESA/SCC Detail Specification No. 9208/001

}s]e}(€

space components coordination group

		Approved by		
lssue/Rev.	Date	SCCG Chairman	ESA Director General or his Deputy	
Issue 4	January 1994	Forman	Lat	
Revision 'A'	February 1995	Poromien's	Home	



. ...

Rev. 'A'

PAGE 2

DOCUMENTATION CHANGE NOTICE

Rev. Letter	Rev. Date	CHANGE Reference Item		Approved DCR No.
		This issue supersedes Issue 3 and incorporates all modifications Revisions 'A', 'B' and 'C' to Issue 3 and the following DCR's:- Cover page DCN Table 1(a) : Lead Material and/or Finish amended for Variants : Variants 11 and 12 added Table 1(b) : No. 2, in Remarks, Note No. amended to "1" : No. 3, in Remarks, Note No. amended to "2" : No. 6, existing temperature specified for DIL/ , new temperature and Note reference CCP : Note 1 renumbered as "2" : Note 2 renumbered as "3" and text amended : Note 3 renumbered as "1" : New Note 4 added Figures 2(a), (b) : Drawing and Table amended	for existing " /FP e added for	None None 22881 23573 23573 23573 23573 23573 23573 23573 23573 23573 23573 23573 23573
		Figures 2(a), (b), (c): Imperial dimensions deletedFigures 2(b), (c): Reference to Note 6 amended to "Note 10"Figure 2(d): New figure addedNotes to Figures: Title of the notes amended: Note 1, last sentence added: Note 8, 'or terminals' added: Note 9, rewritten: Notes 11 and 12 added		22881 23519 22881 22881 22881 22881 22881 22881 22881
		Figure 3(a): Figure for chip carrier package added : Subtitles added above both drawings : Comparison table added : Note 1 addedPara. 4.2.2: PIND deviation deleted, "None" addedPara. 4.2.4: Deviation deleted, "None" addedPara. 4.2.5: Deviation deleted, "None" addedPara. 4.2.5: Deviation deleted, "None" addedPara. 4.2.5: Deviation deleted, "None" addedPara. 4.3.2: Paragraph rewrittenPara. 4.5.2: Paragraph rewrittenPara. 4.5.3: Paragraph rewrittenPara. 4.6.3: "and functional test sequence" deletedPara. 4.7.1: "Tamb" added before " + 22 ± 3°C"Para. 4.8: Title amended	ed to read	22881 22881 22881 21048 22919 22919 23460 22881 23519 23519 23519 23519 23519
'Α'	Feb. '95	P1. Cover Page P2. DCN P15. Para. 4.3.2 : Maximum weights amended		None None 221047

	SEE	ESA/SCC Detail Specification		PAGE	3
		No. 9208/001		ISSUE	4
		TABLE OF CONTENTS			
1.	GENERAL				Page 5
1.1 1.2	Scope Component Type Varia	ote			5 5
1.2	Maximum Ratings				5
1.4	Parameter Derating Inf	ormation			5
1.5	Physical Dimensions				5
1.6	Pin Assignment				5
1.7 1.8	Truth Table Circuit Schematic				5 5
1.0 1.9	Functional Diagram				5
2.	APPLICABLE DOCUM	NENTS			14
3.		S, ABBREVIATIONS, SYMBOLS AND L	JNITS		14
0.		<u>,</u>			
4.	REQUIREMENTS				14
4.1	General				14
4.2	Deviations from Gener				14
4.2.1 4.2.2	Deviations from Special Deviations from Final F				14 14
4.2.2 4.2.3	Deviations from Burn-ii				14
4.2.4	Deviations from Qualifi				14
4.2.5	Deviations from Lot Ac	ceptance Tests			14
4.3	Mechanical Requireme	ents			15
4.3.1	Dimension Check				15
4.3.2 4.4	Weight Materials and Finishes				15 15
4.4 4.4.1	Case				15
4.4.2	Lead Material and Finis	sh			15
4.5	Marking				15
4.5.1	General				15
4.5.2	Lead Identification	Nurahar			15 16
4.5.3 4.5.4	The SCC Component Traceability Information				16
4.6	Electrical Measuremen				16
4.6.1		ts at Room Temperature			16
4.6.2	Electrical Measuremen	ts at High and Low Temperatures			16
4.6.3	Circuits for Electrical N	leasurements			16
4.7 4.7.1	Burn-in Tests Parameter Drift Values				16 16
4.7.1	Conditions for Power E				16
4.7.3	Electrical Circuits for F				16
4.8	Environmental and End				25
4.8.1		ts on Completion of Environmental Tests			25
4.8.2		ts at Intermediate Points during Endurance	e lests		25 25
4.8.3 4.8.4	Electrical Measurement Conditions for Operatin	its on Completion of Endurance Tests			25 25
4.8.4 4.8.5	Electrical Circuits for C	-			25
4.8.6		mperature Storage Test			25

Sec	ESA/SCC Detail Specification No. 9208/001		PAGE ISSUE	4
------------	--	--	---------------	---

TABLES

<u>Page</u>

1(0)	Type Variants	6
1(a)		-
1(b)	Maximum Ratings	6
2	Electrical Measurements at Room Temperature, D.C. Parameters	17
	Electrical Measurements at Room Temperature, A.C. Parameters	18
3	Electrical Measurements at High and Low Temperatures	19
4	Parameter Drift Values	23
5	Conditions for Power Burn-in and Operating Life Test	23
6	Electrical Measurements on Completion of Environmental Tests and at Intermediate	26
	Points and on Completion of Endurance Tests	

FIGURES

1	Not applicable	N/A
2	Physical Dimensions	7
3(a)	Pin Assignment	12
3(b)	Truth Table	12
3(c)	Circuit Schematic	13
3(d)	Functional Diagram	13
4	Circuits for Electrical Measurements	20
5	Electrical Circuit for Power Burn-in and Operating Life Test	24
	NDICES (Applicable to epocific Manufacturers only)	

APPENDICES (Applicable to specific Manufacturers only)'A'Agreed Deviations for Texas Instruments (F)

27

. .



1. GENERAL

1.1 <u>SCOPE</u>

This specification details the ratings, physical and electrical characteristics, test and inspection data for a silicon monolithic, low power bipolar Schottky 9-Bit Odd/Even Parity Generator/Checker, based on Type 54LS280. It shall be read in conjunction with ESA/SCC Generic Specification No. 9000, the requirements of which are supplemented herein.

1.2 COMPONENT TYPE VARIANTS

Variants of the basic type integrated circuits specified herein, which are also covered by this specification, are given in Table 1(a).

1.3 MAXIMUM RATINGS

The maximum ratings, which shall not be exceeded at any time during use or storage, applicable to the integrated circuits specified herein, are as scheduled in Table 1(b).

1.4 PARAMETER DERATING INFORMATION (FIGURE 1)

Not applicable.

1.5 PHYSICAL DIMENSIONS

The physical dimensions of the integrated circuits specified herein are shown in Figure 2.

1.6 PIN ASSIGNMENT

As per Figure 3(a).

1.7 <u>TRUTH TABLE</u>

As per Figure 3(b).

- 1.8 <u>CIRCUIT SCHEMATIC</u> As per Figure 3(c).
- 1.9 FUNCTIONAL DIAGRAM

As per Figure 3(d).



TABLE 1(a) - TYPE VARIANTS

VARIANT	CASE	FIGURE	LEAD MATERIAL AND/OR FINISH
01	FLAT	2(a)	D7
02	FLAT	2(a)	G4
05	DIL	2(b)	D7
06	DIL	2(b)	G4
07	DIL	2(c)	D7
08	DIL	2(c)	D3 or D4
11	CCP	2(d)	7
12	CCP	2(d)	4

TABLE 1(b) - MAXIMUM RATINGS

No.	CHARACTERISTICS	SYMBOL	MAXIMUM RATINGS	UNIT	REMARKS
1	Supply Voltage	V _{CC}	- 0.5 to 7.0	V	-
2	Input Voltage	V _{IN}	- 0.5 to 7.0	V	Note 1
3	Device Dissipation	PD	148.5	mWdc	Note 2
4	Operating Temperature Range	Т _{ор}	– 55 to + 125	°C	-
5	Storage Temperature Range	T _{stg}	– 65 to + 150	°C	-
6	Soldering Temperature For FP and DIP For CCP	T _{sol}	+ 265 + 245	°C	Note 3 Note 4

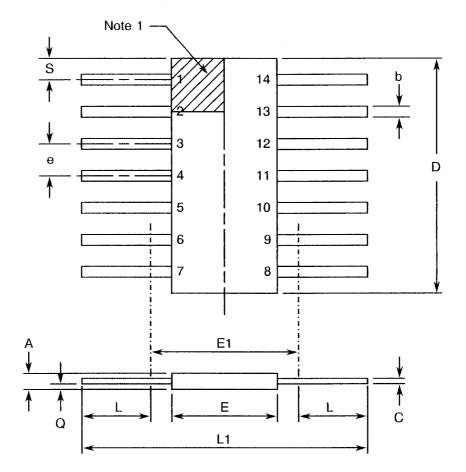
NOTES

- 1. Input current limited to 18mA.
- 2. Must withstand added P_D due to short circuit conditions (i.e. I_{OS}) at one output for 5 seconds.
- 3. Duration 10 seconds maximum at a distance of not less than 1.5mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed.
- 4. Duration 5 seconds maximum and the same terminal shall not be resoldered until 3 minutes have elapsed.



FIGURE 2 - PHYSICAL DIMENSIONS

FIGURE 2(a) - FLAT PACKAGE



SYMBOL	MILLIMETRES		NOTES
STNDUL	MIN	MAX	NOTES
A	1.27	2.03	
b	0.38	0.56	8
С	0.08	0.23	8
D	8.56	8.89	4
E	5.97	6.73	
E1	7.00 TY	(PICAL	4
е	1.27 TY	PICAL	5, 9
L	6.86	8.00	8
L1 ·	21.34	21.84	
Q	0.51	1.02	2
S	0.25	0.64	7



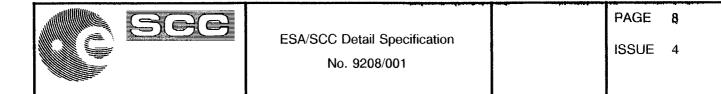
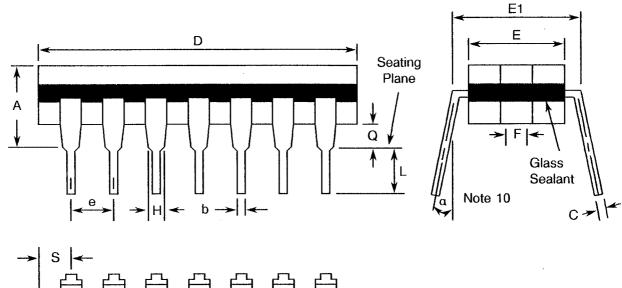
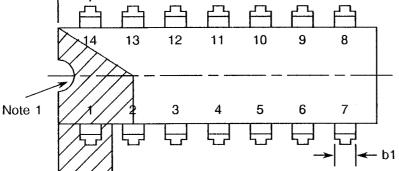


FIGURE 2 - PHYSICAL DIMENSIONS (CONTINUED)

FIGURE 2(b) - DUAL-IN-LINE PACKAGE



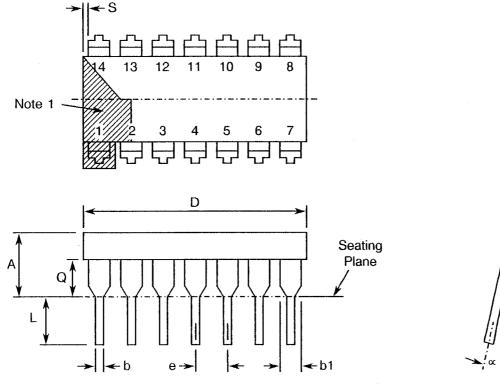


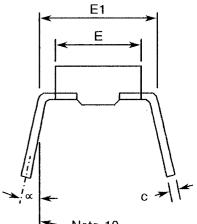
SYMBOL	MILLIMETRES		NOTES
STMBOL	MIN	MAX	NOTES
А	-	5.08	
b	0.38	0.66	8
b1	-	1.78	8
С	0.20	0.44	8
D	19.18	19.94	4
E	6.22	7.62	4
E1	7.37	8.13	
е	2.54 TY	/PICAL	6, 9
F	1.27 TY	(PICAL	
Н	0.76	-	8
L.	3.30	5.08	8
Q	0.51	-	3
S	1.78	2.54	7
a	0°	15°	10



FIGURE 2 - PHYSICAL DIMENSIONS (CONTINUED)

FIGURE 2(c) - DUAL-IN-LINE PACKAGE





-	Note	10
---	------	----

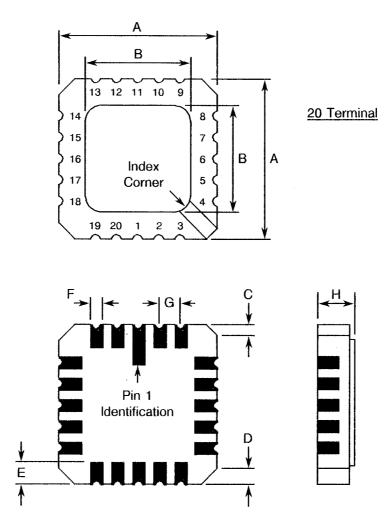
SYMBOL	MILLIMETRES		NOTES	
STWBUL	MIN.	MAX.	NUTES	
A	-	5.08	-	
b	0.36	0.58	8	
b1	0.76	1.78	8	
с	0.20	0.38	8	
D	16.26	19.96	-	
E	5.59	7.87	-	
E1	7.37	8.13	4	
е	2.54 T\	PICAL	6, 9	
L	3.18	5.08	-	
· Q	0.38	2.03	3	
S	0.25	1.35	7	
x	0°	15°	10	

NOTES: See Page 11.



FIGURE 2 - PHYSICAL DIMENSIONS (CONTINUED)

FIGURE 2(d) - SQUARE CHIP CARRIER PACKAGE (3 LAYER BASE)



SYMBOL	MILLIM	NOTES	
STMBOL	MIN. MAX.		NOTES
A	8.687	9.093	-
В	7.798	9.093	- 1
С	0.250	0.510	11
D	0.889	1.143	12
E	1.140	1.400	8
F	0.559	0.712	8
G	1.27 T)	5, 9	
н	1.630	2.540	-

NOTES: See Page 11.



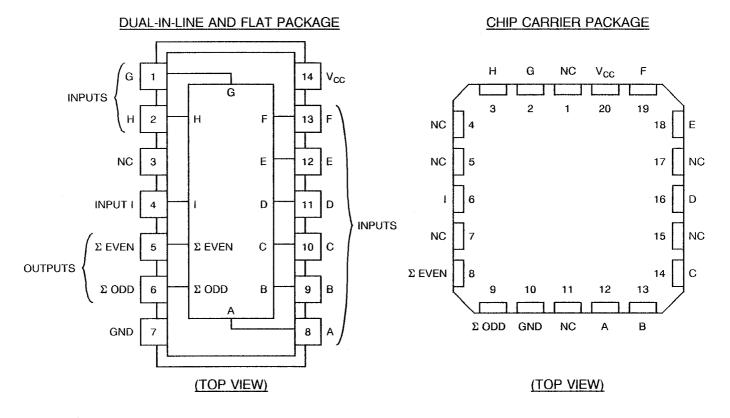
FIGURE 2 - PHYSICAL DIMENSIONS (CONTINUED)

NOTES TO FIGURES 2(a) TO 2(d)

- 1. Index area: a notch or a dot shall be located adjacent to Pin 1 and shall be within the shaded area shown. For chip carrier packages, the index shall be as shown in Figure 2(d).
- 2. Dimension Q shall be measured at the point of exit of the lead from the body.
- 3. Dimension Q shall be measured from the seating plane to the base plane.
- 4. This dimension allows for off-centre lids, meniscus and glass overrun.
- 5. The true position pin spacing is 1.27mm between centrelines. Each pin centreline shall be located within ±0.13mm of its true longitudinal position relative to Pins 1 and 14.
- 6. The true position pin spacing is 2.54mm between centrelines. Each pin centreline shall be located within ±0.25mm of its true longitudinal position relative to Pins 1 and 14.
- 7. Applies to all four corners.
- 8. All leads or terminals.
- 12 spaces for flat and dual-in-line packages.
 16 spaces for chip carrier packages.
- 10. Lead centre when α is 0°.
- 11. Index corner only 2 dimensions.
- 12. 3 non-index corners 6 dimensions.

	ESA/SCC Detail Specification No. 9208/001		PAGE 12 ISSUE 4
--	--	--	--------------------

FIGURE 3(a) - PIN ASSIGNMENT



FLAT PACKAGE AND DUAL-IN-LINE TO CHIP CARRIER PIN ASSIGNMENT

FLAT PACKAGE AND DUAL-IN-LINE PIN OUTS	1	2	3	4	5	6	7	8	9	10	11	12	13	14
CHIP CARRIER PIN OUTS	2	3	4	6	8	9	10	12	13	14	16	18	19	20

NOTES

1. All references throughout this specification relate to FLAT/DIL packages only.

FIGURE 3(b) - TRUTH TABLE (FUNCTION TABLE)

NUMBER OF INPUTS A THRU I	Ουτι	PUTS
THAT ARE HIGH	Σ EVEN	Σ ODD
0, 2, 4, 6, 8	Н	L
1, 3, 5, 7, 9	L	Н

NOTES

1. Logic Level Definitions: L = Low Level, H = High Level.

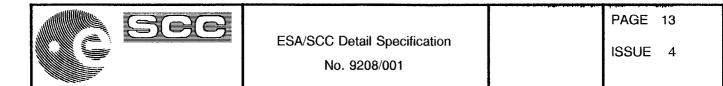
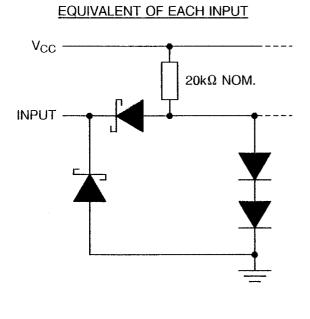
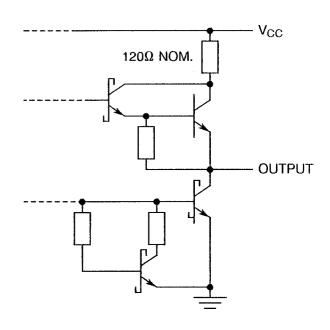


FIGURE 3(c) - CIRCUIT SCHEMATIC

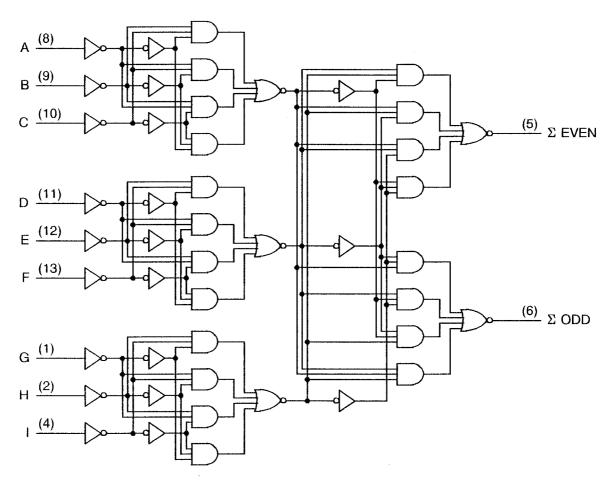
TYPICAL OF ALL OUTPUTS





· · ·

FIGURE 3(d) - FUNCTIONAL DIAGRAM





2. APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:-

- (a) ESA/SCC Generic Specification No. 9000 for Integrated Circuits.
- (b) MIL-STD-883, Test Methods and Procedures for Micro-electronics.

3. TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESA/SCC Basic Specification No. 21300 shall apply. In addition, the following abbreviations are used:-

V_{IC} = Input Clamp Voltage.

I_{CC} = Supply Current.

V_{CC} = Supply Voltage.

4. **REQUIREMENTS**

4.1 <u>GENERAL</u>

The complete requirements for procurement of the integrated circuits specified herein are stated in this specification and ESA/SCC Generic Specification No. 9000 for Integrated Circuits. Deviations from the Generic Specification applicable to this specification only, are listed in Para. 4.2.

Deviations from the applicable Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESA/SCC requirements and do not affect the components' reliability, are listed in the appendices attached to this specification.

4.2 DEVIATIONS FROM GENERIC SPECIFICATION

- 4.2.1 <u>Deviations from Special In-process Controls</u> None.
- 4.2.2 Deviations from Final Production Tests (Chart II)

None.

4.2.3 Deviations from Burn-in Tests (Chart III)

- (a) Para. 7.1.1(a), High Temperature Reverse Bias tests and subsequent electrical measurements related to this test shall be omitted.
- (b) Para. 9.9.2, Electrical Measurements at High and Low Temperatures: Only a test result summary, based on go-no-go tests and presented in histogram form is required.
- 4.2.4 <u>Deviations from Qualification Tests (Chart IV)</u> None.
- 4.2.5 <u>Deviations from Lot Acceptance Tests (Chart V)</u> None.



PAGE 15

4.3 MECHANICAL REQUIREMENTS

4.3.1 Dimension Check

The dimensions of the integrated circuits specified herein shall be checked. They shall conform to those shown in Figure 2.

4.3.2 Weight

The maximum weight of the integrated circuits specified herein shall be 0.7 grammes for the flat package, 2.2 grammes for the dual-in-line package and 0.6 grammes for the chip carrier package.

4.4 MATERIALS AND FINISHES

The materials and finishes shall be as specified herein. Where a definite material is not specified, a material which will enable the integrated circuits specified herein to meet the performance requirements of this specification shall be used. Acceptance or approval of any constituent material does not guarantee acceptance of the finished product.

4.4.1 <u>Case</u>

The case shall be hermetically sealed and have a metal body with hard glass seals or a ceramic body and the lids shall be welded, brazed, preform-soldered or glass frit-sealed.

4.4.2 Lead Material and Finish

For dual-in-line and flat packages, the material shall be either Type 'D' or Type 'G' with either Type '3 or 4', Type '4' or Type '7' finish in accordance with the requirements of ESA/SCC Basic Specification No. 23500. For chip carrier packages, the finish shall be either Type '4' or Type '7' in accordance with the requirements of ESA/SCC Basic Specification No. 23500. (See Table 1(a) for Type Variants).

4.5 <u>MARKING</u>

4.5.1 General

The marking of all components delivered to this specification shall be in accordance with the requirements of ESA/SCC Basic Specification No. 21700. Each component shall be marked in respect of:-

- (a) Lead Identification.
- (b) The SCC Component Number.
- (c) Traceability Information.

4.5.2 Lead Identification

For dual-in-line and flat packages, an index shall be located at the top of the package in the position defined in Note 1 to Figure 2 or, alternatively, a tab may be used to identify Pin No. 1. The pin numbering must be read with the index or tab on the left-hand side. For chip carrier packages, the index shall be as defined by Figure 2(d).



4.5.3 The SCC Component Number

Each component shall bear the SCC Component Number which shall be constituted and marked as follows:

	<u>920800102B</u>
Detail Specification Number	
Type Variant (see Table 1(a))	
Testing Level (B or C, as applicable)	

4.5.4 <u>Traceability Information</u>

Each component shall be marked in respect of traceability information in accordance with the requirements of ESA/SCC Basic Specification No. 21700.

4.6 ELECTRICAL MEASUREMENTS

4.6.1 Electrical Measurements at Room Temperature

The parameters to be measured in respect of electrical characteristics are scheduled in Table 2. Unless otherwise specified, the measurements shall be performed at T_{amb} = +22±3 °C.

4.6.2 Electrical Measurements at High and Low Temperatures

The parameters to be measured at high and low temperatures are scheduled in Table 3. The measurements shall be performed at T_{amb} = +125 and -55 °C respectively.

4.6.3 <u>Circuits for Electrical Measurements</u>

Circuits for use in performing the electrical measurements listed in Tables 2 and 3 of this specification are shown in Figure 4.

4.7 BURN-IN TESTS

4.7.1 Parameter Drift Values

The parameter drift values applicable to burn-in are specified in Table 4 of this specification. Unless otherwise stated, measurements shall be performed at $T_{amb} = +22 \pm 3$ °C. The parameter drift values (Δ) applicable to the parameters scheduled, shall not be exceeded. In addition to these drift value requirements, the appropriate limit value specified for a given parameter in Table 2 shall not be exceeded.

4.7.2 Conditions for Power Burn-in

The requirements for power burn-in are specified in Section 7 of ESA/SCC Generic Specification No. 9000. The conditions for power burn-in shall be as specified in Table 5 of this specification.

4.7.3 Electrical Circuits for Power Burn-in

Circuits for use in performing the power burn-in tests are shown in Figure 5 of this specification.



TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - D.C. PARAMETERS

No.	CHARACTERISTICS	SYMBOL	TEST METHOD	TEST	TEST CONDITIONS	LIM	ITS	UNIT
NO.		STMDOL	MIL-STD 883	FIG.	(PINS UNDER TEST)	MIN	МАХ	UNIT
1	Functional Test	-	-	3(b)	Verify Truth Table with Load. Note 1	1	-	-
2 to 10	Input Current High Level 1	l _{iH1}	3010	4(a)	V _{CC} = 5.5V, V _{IN} = 2.7V (Pins 1-2-4-8-9-10-11-12- 13)	-	20	μA
11 to 19	Input Current High Level 2 (Max. Input Voltage)	I _{IH2}	3010	4(a)	V _{CC} = 5.5V, V _{IN} = 7.0V (Pins 1-2-4-8-9-10-11-12- 13)	-	100	μA
20 to 28	Input Clamp Voltage	V _{IC}	3009	4(b)	V _{CC} = 4.5V, I _{IN} = - 18mA Note 2 (Pins 1-2-4-8-9-10-11-12- 13)	-	- 1.5	V
29 to 37	Input Current Low Level	l _{IL}	3009	4(c)	V _{CC} = 5.5V, V _{IL} = 0.4V (Pins 1-2-4-8-9-10-11-12- 13)	-	- 400	μА
38 to 39	Output Voltage Low Level	V _{OL}	3007	4(d)	$V_{CC} = 4.5V, V_{IL} = 0.7V$ $V_{IH} = 2.0V, I_{OL} = 4.0mA$ (Pins 5-6)	-	0.4	V
40 to 41	Output Voltage High Level	V _{OH}	3006	4(e)	V _{CC} = 4.5V, V _{IL} = 0.7V V _{IH} = 2.0V, I _{OH} = - 400µA (Pins 5-6)	2.5	-	V
42 to 43	Short Circuit Output Current	los	3011	4(f)	V _{CC} = 5.5V Note 3 (Pins 5-6)	- 15	- 100	mA
44	Supply Current	Icc	3005	4(g)	V _{CC} = 5.5V All Outputs Open. All Inputs at Ground. (Pin 14)	-	27	mA

NOTES: See Page 18.



TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - A.C. PARAMETERS

No.		HARACTERISTICS SYMBOL MIL OTD FIG (PINS UNDER TEST)		LIMITS		UNIT		
		STMBOL	MIL-STD 883	FIG.	(NOTE 4)	MIN	МАХ	UNIT
45	Propagation Delay,	t _{PLH}	3003	4(h)	$V_{\rm CC} = 5.0V$	-	50	ns
to 49	Low to High Level, from Data to Σ Even				$R_L = 2.0 k\Omega$ $C_L = 15 pF$			
50	Propagation Delay,	t _{PHL}			(Pin 5)	-	45	
to 54	High to Low Level, from Data to Σ Even							
55	Propagation Delay,	t _{PLH}	3003	4(h)	$V_{\rm CC} = 5.0V$	-	35	ns
to 59	Low to High Level, from Data to Σ Odd				$R_L = 2.0 k\Omega$ $C_L = 15 pF$			
60	Propagation Delay,	t _{PHL}			(Pin 6)	-	50	
to 64	High to Low Level, from Data to Σ Odd							

NOTES

- 1. Go-no-go test with $V_{IL} = 0.3V$; $V_{IH} = 3.0V$; trip point 1.5V.
- 2. All inputs and outputs not under test shall be open.
- 3. No more than one output should be shorted at a time, and only for 1 second maximum.
- 4. Propagation delay measurements shall be performed as a go-no-go test on a 100% basis. Read-and-record measurements shall be performed on an LTPD7 sample basis following the Chart III Burn-in Test.



- ---

TABLE 3 - ELECTRICAL MEASUREMENTS AT HIGH AND LOW TEMPERATURES, + 125(+0-5) °C AND - 55(+5-0) °C

No.	CHARACTERISTICS	SYMBOL	TEST METHOD	TEST	TEST CONDITIONS	LIM	ITS	UNIT
INO.	CHARACTERIS 1103	STMBOL	MIL-STD 883	FIG.	(PINS UNDER TEST)	MIN	MAX	UNIT
1	Functional Test	-	-	3(b)	Verify Truth Table with Load. Note 1	-	-	-
2 to 10	Input Current High Level 1	l _{IH1}	3010	4(a)	V _{CC} = 5.5V, V _{IN} = 2.7V (Pins 1-2-4-8-9-10-11-12- 13)	-	20	μA
11 to 19	Input Current High Level 2 (Max. Input Voltage)	I _{IH2}	3010	4(a)	V _{CC} = 5.5V, V _{IN} = 7.0V (Pins 1-2-4-8-9-10-11-12- 13)	-	100	μА
20 to 28	Input Clamp Voltage	V _{IC}	3009	4(b)	V _{CC} = 4.5V, I _{IN} = - 18mA Note 2 (Pins 1-2-4-8-9-10-11-12- 13)	-	- 1.5	V
29 to 37	Input Current Low Level	Ι _{ΙL}	3009	4(c)	V _{CC} = 5.5V, V _{IL} = 0.4V (Pins 1-2-4-8-9-10-11-12- 13)	-	- 400	μА
38 to 39	Output Voltage Low Level	V _{OL}	3007	4(d)	V _{CC} = 4.5V, V _{IL} = 0.7V V _{IH} = 2.0V, I _{OL} = 4.0mA (Pins 5-6)	-	0.4	V
40 to 41	Output Voltage High Level	V _{OH}	3006	4(e)	$V_{CC} = 4.5V, V_{IL} = 0.7V$ $V_{IH} = 2.0V, I_{OH} = -400\mu A$ (Pins 5-6)	2.5	-	V
42 to 43	Short Circuit Output Current	los	3011	4(f)	V _{CC} = 5.5V Note 3 (Pins 5-6)	- 15	- 100	mA
44	Supply Current	lcc	3005	4(g)	V _{CC} = 5.5V All Outputs Open. All Inputs at Ground. (Pin 14)	-	27	mA

NOTES: See Page 18.

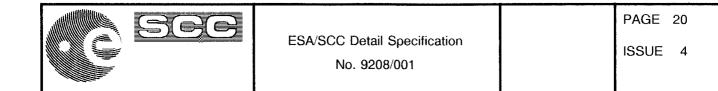
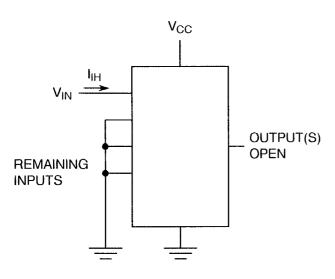
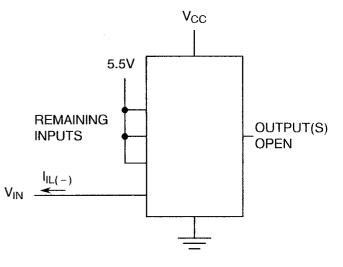


FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS

FIGURE 4(a) - INPUT CURRENT HIGH LEVEL

FIGURE 4(b) - INPUT CLAMP VOLTAGE





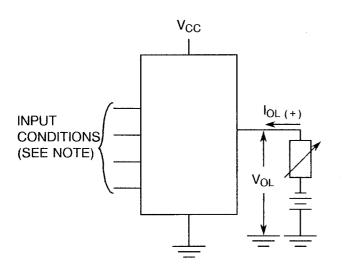
NOTES

1. Test each input separately.

NOTES

1. Test each input separately.

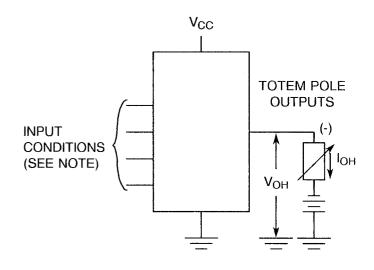
FIGURE 4(c) - LOW LEVEL INPUT CURRENT



NOTES

1. Test each input separately.

FIGURE 4(d) - LOW LEVEL OUTPUT VOLTAGE



- -- -

- NOTES
- 1. Test per Truth Table.

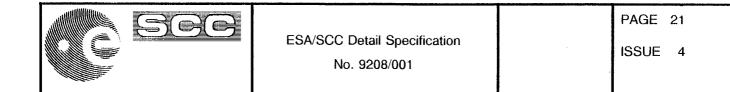
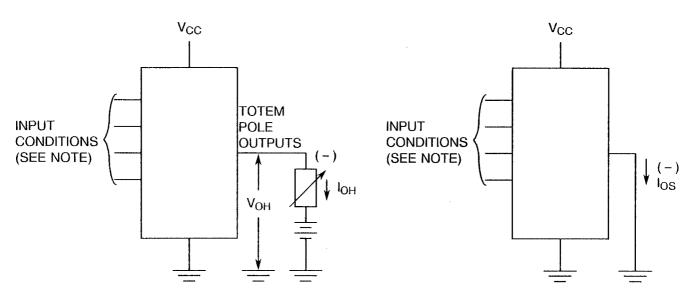


FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS (CONTINUED)

FIGURE 4(e) - HIGH LEVEL OUTPUT VOLTAGE

FIGURE 4(f) - SHORT CIRCUIT OUTPUT CURRENT



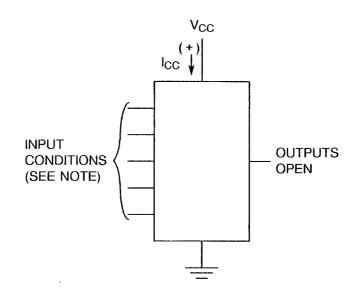
NOTES

1. Test per Truth Table.

<u>NOTES</u>

- 1. No more than one output should be shorted at a time
- 2. Test per Truth Table.

FIGURE 4(g) - SUPPLY CURRENT



NOTES

1. All inputs at Ground.

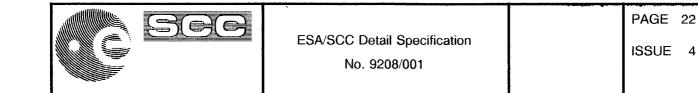
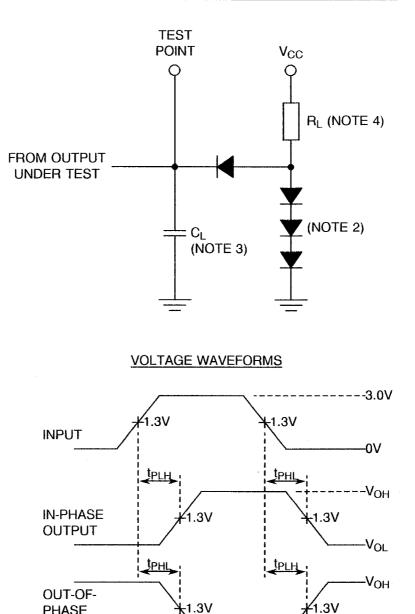


FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS (CONTINUED)

FIGURE 4(h) - DYNAMIC TEST AND SWITCHING WAVEFORMS



---V_{OL}

<u>NOTES</u> 1. Input pulse characteristics: $t_r \le 15$ ns, $t_f \le 6.0$ ns, PRR ≤ 1.0 MHz.

PHASE OUTPUT

- 2. All diodes are 1N916 or 1N3064.
- 3. $C_L = 15 pF$.
- 4. $R_L = 2.0 k \Omega$.



TABLE 4 - PARAMETER DRIFT VALUES

No.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR TEST METHOD	TEST CONDITIONS	CHANGE LIMITS (Δ)	UNIT
2 to 10	Input Current High Level 1	l _{iH1}	As per Table 2	As per Table 2	±20 or (1) ±0.5	% µА
29 to 37	Input Current Low Level	l _{iL}	As per Table 2	As per Table 2	± 18	μA
38 to 39	Output Voltage Low Level	V _{OL}	As per Table 2	As per Table 2	±60	mV
40 to 41	Output Voltage High Level	V _{OH}	As per Table 2	As per Table 2	±240	mV

NOTES

1. Whichever is greater, referred to the initial value.

TABLE 5 - CONDITIONS FOR POWER BURN-IN AND OPERATING LIFE TEST

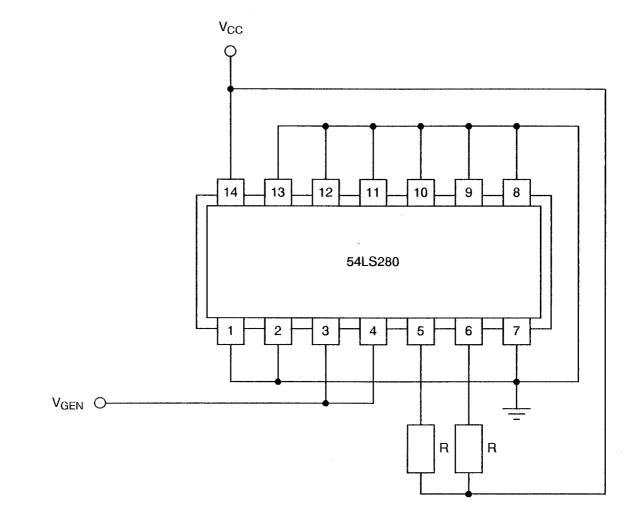
No.	CHARACTERISTICS	SYMBOL	CONDITION	UNIT
1	Ambient Temperature	T _{amb}	+ 125(+ 0 – 5)	°C
2	Power Supply Voltage	V _{CC}	5(+ 0.5 - 0)	V
3	Pulse Voltage	V _{GEN}	0.5 max. to 3.0 min.	V
4	Frequency	f	100 (Note 1)	Hz
5	Fan-out	-	10	-
6	Rise Time	tr	50 max.	μs
7	Fall Time	t _f	50 max.	μs
8	Duty Cycle	-	20 min.	%

NOTES

1. Tolerance $\pm 10\%$.



FIGURE 5 - ELECTRICAL CIRCUIT FOR POWER BURN-IN AND OPERATING LIFE TEST





 $\frac{\text{NOTES}}{1. R = 1.2k\Omega}.$



4.8 <u>ENVIRONMENTAL AND ENDURANCE TESTS (CHARTS IV AND V OF ESA/SCC GENERIC</u> <u>SPECIFICATION NO. 9000)</u>

4.8.1 Electrical Measurements on Completion of Environmental Tests

The parameters to be measured on completion of environmental tests are scheduled in Table 6. Unless otherwise stated, the measurements shall be performed at $T_{amb} = +22 \pm 3$ °C.

4.8.2 Electrical Measurements at Intermediate Points during Endurance Tests

The parameters to be measured at intermediate points during endurance tests are as scheduled in Table 6 of this specification.

4.8.3 Electrical Measurements on Completion of Endurance Tests

The parameters to be measured on completion of endurance testing are as scheduled in Table 6 of this specification. Unless otherwise stated, the measurements shall be performed at $T_{amb} = +22 \pm 3 \text{ °C}.$

4.8.4 Conditions for Operating Life Tests

The requirements for operating life testing are specified in Section 9 of ESA/SCC Generic Specification No. 9000. The conditions for operating life testing shall be as specified in Table 5 of this specification.

4.8.5 <u>Electrical Circuits for Operating Life Tests</u>

Circuits for use in performing the operating life tests are shown in Figure 5.

4.8.6 Conditions for High Temperature Storage Test

The requirements for the high temperature storage test are specified in ESA/SCC Generic Specification No. 9000. The conditions for high temperature storage shall be $T_{amb} = +150(+0.5)$ °C.



TABLE 6 - ELECTRICAL MEASUREMENTS ON COMPLETION OF ENVIRONMENTAL TESTS AND AT INTERMEDIATE POINTS AND ON COMPLETION OF ENDURANCE TESTS

No.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR	TEST	CHAN	UNIT	
140.	OF A HAO TENIS TIOS	STWDOL	TEST METHOD	CONDITIONS	(Δ)	ABSOLUTE	UNIT
2 to 10	Input Current High Level 1	l _{IH1}	As per Table 2	As per Table 2	± 1.0	-	μA
11 to 19	Input Current High Level 2	I _{IH2}	As per Table 2	As per Table 2	-	100	μA
29 to 37	Input Current Low Level	l _{iL}	As per Table 2	As per Table 2	± 12	-	μА
38 to 39	Output Voltage Low Level	V _{OL}	As per Table 2	As per Table 2	± 60	-	mV
40 to 41	Output Voltage High Level	V _{OH}	As per Table 2	As per Table 2	±240	-	mV
44	Supply Current	I _{CCH}	As per Table 2	As per Table 2	± 20	-	%



APPENDIX 'A'

Page 1 of 1

AGREED DEVIATIONS FOR TEXAS INSTRUMENTS (F)

ITEMS AFFECTED	DESCRIPTION OF DEVIATIONS
Para. 4.2.1	Scanning Electron Microscope (SEM) Inspection may be performed using TIF document TIF 3.61.610.001.
Para. 4.2.2	Prior to Die Shear Test TIF may perform a Radiographic Inspection on the randomly chosen samples to be subjected to this test, using TIF document TIF 50.42-3002.
Para. 4.2.3	Radiographic Inspection may be performed using TIF document TIF 50.42-3002.